



The New Millennium Program

Towards a Spacecraft on a Chip

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Outline:

- 1. A Historic Perspective
- 2. A Vision for the New Millennium
- Integrated Product Development Team (IPDT)
 Technology Roadmap
 - 3D VLSI Architecture Technology Development
 - Low Power Electronics Technology Development
- 4. Deep-Space 1 and 2 Avionics Architectures
- 5. Customers and Partners

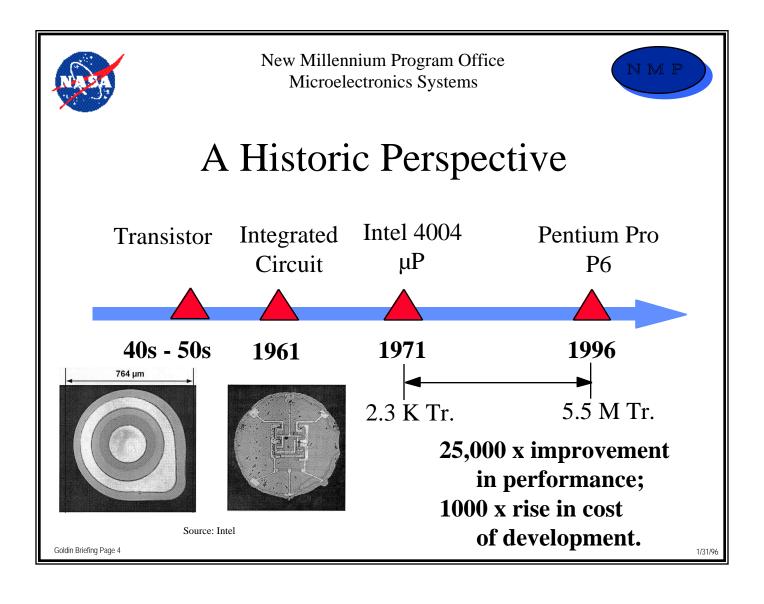
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A Historic Perspective

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A Historic Perspective

Perhaps more than any other single technology of the 20th century, semiconductor microelectronics technology has transformed almost every aspect of modern society:

- Information Technologies
- Transportation
- Communication
- Science and Education
- Medicine
- Design, automation, and manufacturing
- Entertainment

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A Historic Perspective

Stone Age

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Bronze Age

3000 BCE East Anatolia 1000 BCE Middle East

Iron Age

Middle East, Europe

Silicon Age

Stone, Bronze, Iron, Silicon Age



1948

Silicon Valley, USA





A Vision for the New Millennium

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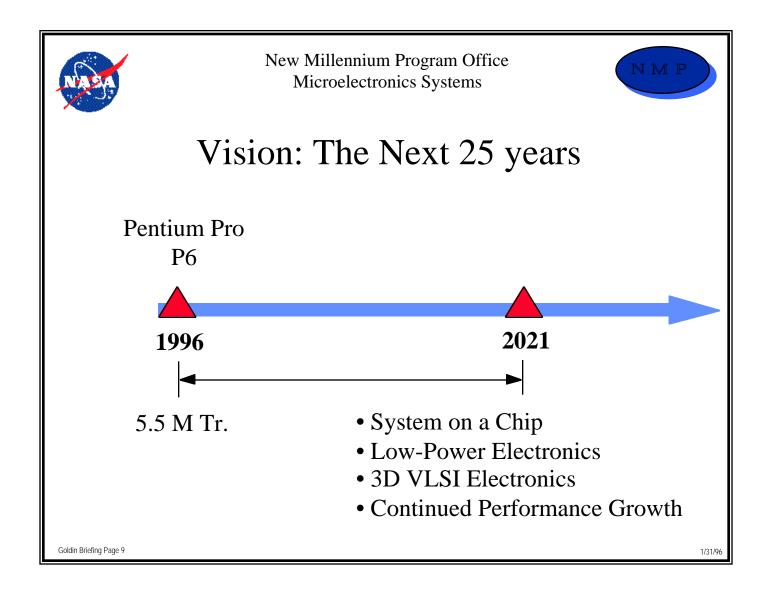


Vision: The Next 25 years

"Every 18 months microprocessors double in speed. Within 25 years, one computer will be as powerful as all those in the Silicon Valley."

> David A. Patterson Professor, UC Berkeley Scientific American September 1995

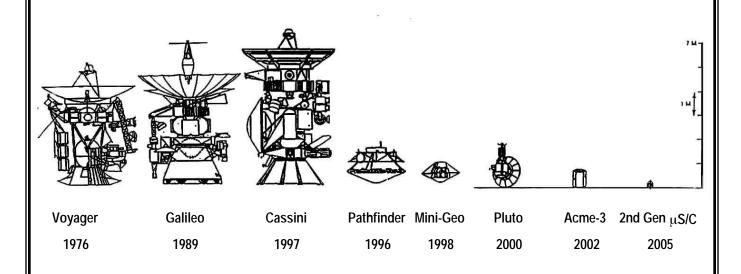
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Towards the Second Generation Spacecraft

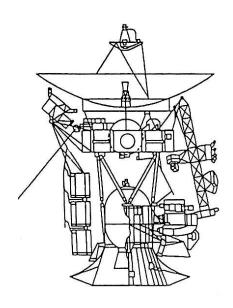


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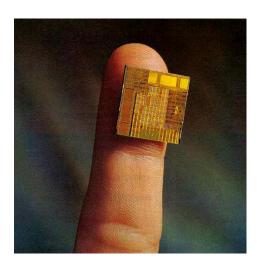


Vision: A Spacecraft on a Chip



 $\begin{array}{c} VOYAGER \\ VOLUME = 62 \ m^3 \\ MASS \ (DRY) = 986 \ kg \\ POWER = 430 \ W \end{array}$

SYSTEM ON A CHIP



PowerPC 620 5 • 10⁶ Transistors

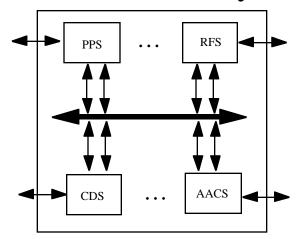
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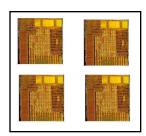
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From Subsystems to Macro-Cells

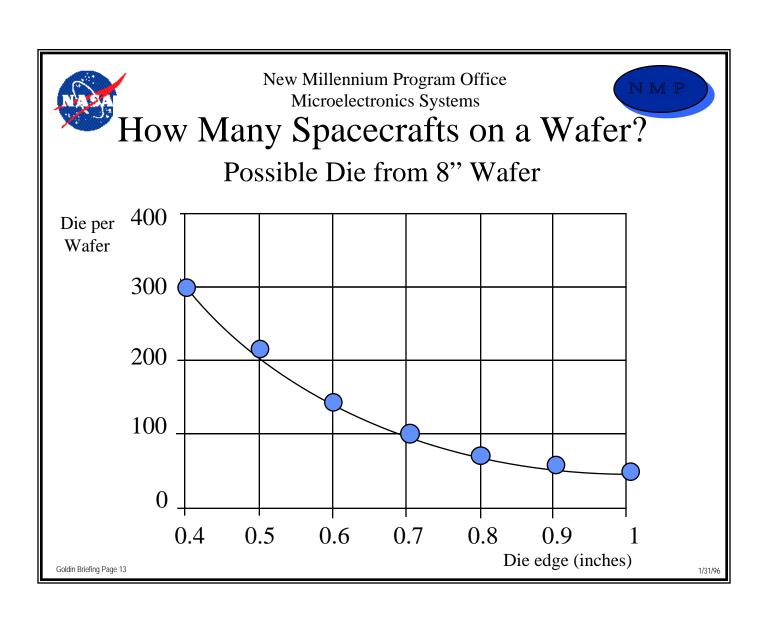




Programmable macro-cells on a single chip

- CAD Synthesis of Spacecraft "System"
- Integration and test has a new meaning
- Spacecraft cabling is replaced by sub-micron metal interconnect
- How many Spacecraft can fit on one wafer?

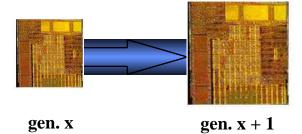
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Increasing functional density while reducing cost per function.



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The basis for the sustained growth of the semiconductor industry is the exponential growth of functional density and the 30% per year, per function reduction in cost due to:

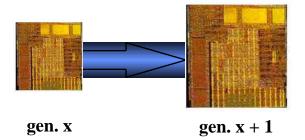
- Design innovation
- Device shrinkage
- Wafer size increase
- Die size increase
- Yield improvement
- Improvement in capital equipment utilization

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The semiconductor industry yield is at an all-time high!



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Electrical Defect Density

| Year | '95 | '98 | '01 | '04 | '07 | '10 |
|-------------------|------|------|------|------|------|------|
| Feature Size (µm) | 0.35 | 0.25 | 0.18 | 0.13 | 0.10 | 0.07 |
| d/m² | 240 | 160 | 140 | 120 | 100 | 25 |

Yield 90%

Source: SIA '95

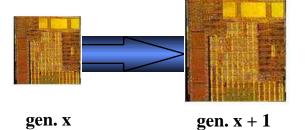
[d/m²] is a mathematical model based on statistical evidence of those defects that cause a chip to electrically fail. It is independent of chip size.

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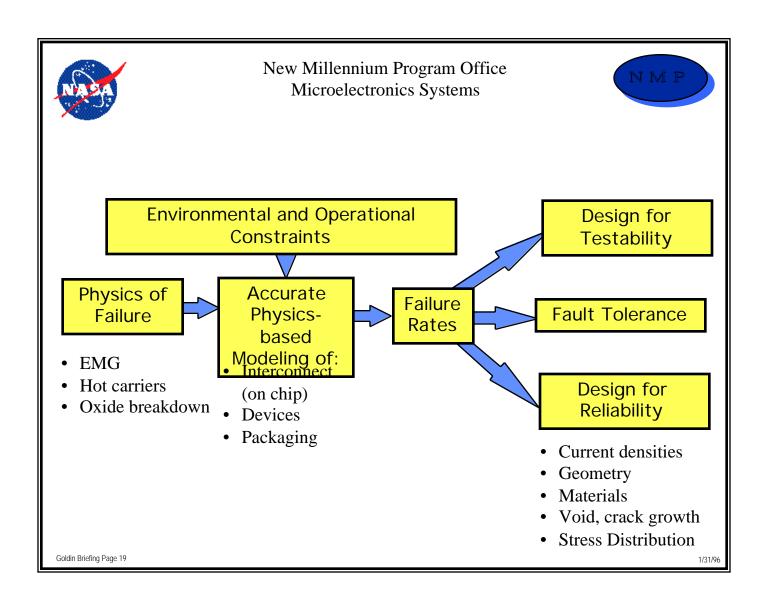




Improving functional reliability.



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Integrated Product Development Team Technology Roadmap

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Key Capability Needs for the 21st Century

- Develop reduction of all spacecraft electronics mass,
 volume and power by two orders of magnitude relative to
 the state-of-the art in space flight computing
- Accelerated insertion of commercial technology, components, and processes into space flight applications for the reduction of the total spacecraft life-cycle cost
- Scaleable and fault-tolerant on-board computing architectures that will enable autonomous spacecraft control and operation, and on-board science data analysis, for the purpose of reducing the total system cost, and increase the mission scientific return.

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Candidate High-Priority Technologies

- Highly integrated and modular 3D avionics architectures amenable to industry standardization
- Integrated power management electronics
- Advanced microelectronics packaging technologies such as Multichip Modules (MCMs), 3d chip stacking, and MCM stacking
- Low power electronics
- High-density low-power data storage technology
- High-bandwidth low-power interfaces
- Scaleable on-board real-time and reliable multiprocessing
- Fault tolerant computing
- Techniques for rapid prototyping

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Industry Roadmap Team

| Technology Area | Members | | |
|-------------------|--|--|--|
| Semiconductors | MIT/LL - Craig Keast Loral - Bob Delean | | |
| Processors | Loral - Bob Delean AFPL - Captain Ronald Marx (LM) - Gerhard Franz | | |
| Storage | Honeywell - John Samson TRW - Darby Lee tarry | | |
| I/O | TRW - Darby Lee Terry Optivision - Robert Kalman Boeing - Warren Snapp | | |
| Packaging | LM - Gerhard Franz SCC - Nicholas Tenenketges UCSD - Volkan Ozguz GIT - Abhijit Chatterjee | | |
| Power | LM - Gerhard Franz Boeing - Warren Snapp | | |
| Design Automation | USC - Massoud Pedram GIT - Abhijit Chatterjee | | |

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SEMICONDUCTOR INDUSTRY ASSOCIATION ROADMAP

| YEAR OF FIRST DRAM SHIPMENT | 1995 | 1998 | 2001 | 2004 | 2007 | 2010 |
|--|-------|-----------|-----------|-------|--------|--------|
| MINIMUM FEATURE (μm) | 0.35 | 0.25 | 0.18 | 0.13 | 0.10 | 0.07 |
| Memory | | 05/11 | 40 | | 440 | |
| Bits/Chip (DRAM/Flash) | 64M | 256M | 1G | 4G | 16G | 64G |
| Cost/Bit @ volume (millicents) | 0.017 | 0.007 | 0.003 | 0.001 | 0.0005 | 0.0002 |
| Logic (High Volume: Microprocessor) | | | 4014 | 0=14 | | |
| Locig Transistors/cm ² (packed) | 4M | 7M | 13M | 25M | 50M | 90M |
| Bits/cm ² (cache SRAM) | 2M | 6M | 20M | 50M | 100M | 300M |
| Cost/Transistor @ volume (millicents) | 1 | 0.5 | 0.2 | 0.1 | 0.05 | 0.02 |
| Logic (Low Volume: ASIC) | | | | | | |
| Transistors/cm² (auto layout) | 2M | 4M | 7M | 12M | 25M | 40M |
| Non-recurring engineering | 0.3 | 0.1 | 0.05 | 0.03 | 0.02 | 0.01 |
| cost/transistor (milicents) | | | | | | |
| Chip Frequency (MHz) | | | | | | |
| On-chip clock, cost-performance | 150 | 200 | 300 | 400 | 500 | 625 |
| On-chip clock, high-performance | 300 | 450 | 600 | 800 | 1000 | 1100 |
| Chip-to-board speed, high performance | 150 | 200 | 250 | 300 | 375 | 475 |
| Chip Size (mm ²) | | | | | | |
| DRAM | 190 | 280 | 420 | 640 | 960 | 1400 |
| Microprocessor | 250 | 300 | 360 | 430 | 520 | 620 |
| ASIC | 450 | 660 | 750 | 900 | 1100 | 1400 |
| Power Supply Voltage (V) | | | | | | |
| Desktop | 3.3 | 2.5 | 1.8 | 1.5 | 1.2 | 0.9 |
| Battery | 25 | 1.8 - 2.5 | 0.9 - 1.8 | 0.9 | 0.9 | 0.9 |

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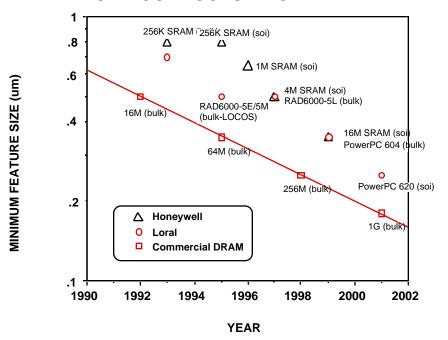




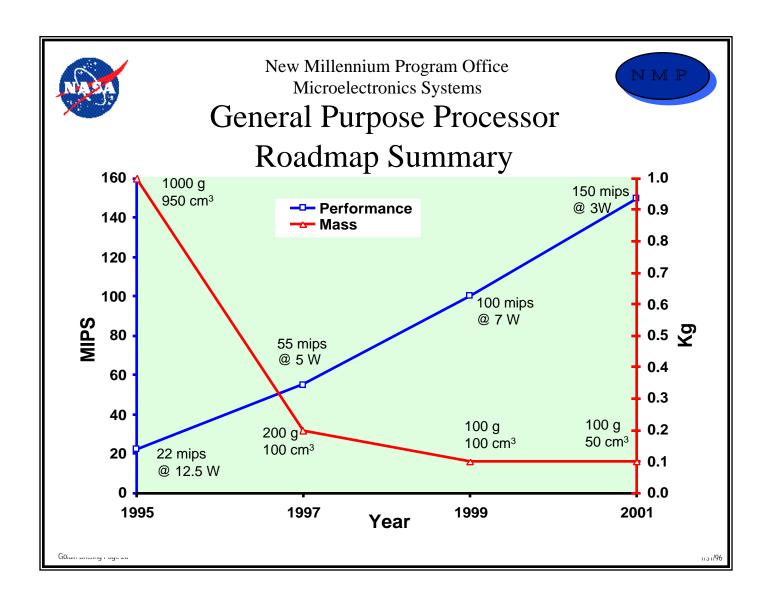
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Microelectronics Feature Size

SPACE COMPONENT MINIMUM FEATURE SIZE SEMICONDUCTOR ROADMAP



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Packaging Roadmap Summary

- Vision: Towards 3D VLSI
- Metrics: level of integration, size, mass, power density.

| • Roadmap: <u>Low-cos</u> | Roadmap: <u>Low-cost 3D MCM + HDI</u> | | <u>3D VLSI</u> | |
|----------------------------------|---------------------------------------|---------------|--|--|
| | 97 | 99 | 01 | |
| Integration | medium | high | very high | |
| Volume (cc) (dgtl+pwr) | 600+1000 | 400+500 | 70+100 | |
| Mass (g) (dgtl+pwr) | 1000+2000 | 500+500 | 300+300 | |
| Capabilities | Some HDI | 3D HDI | 3D HDI | |
| | Mixed MCM | 3D VLSI | 3D VLSI | |
| //Com | MCM/SMT | 3D Stack PCBs | 3D MCM | |
| | 3D Stack PCBs | | | |
| | Si chi | | Carrier Substrate 800 μm thick AIN) | |
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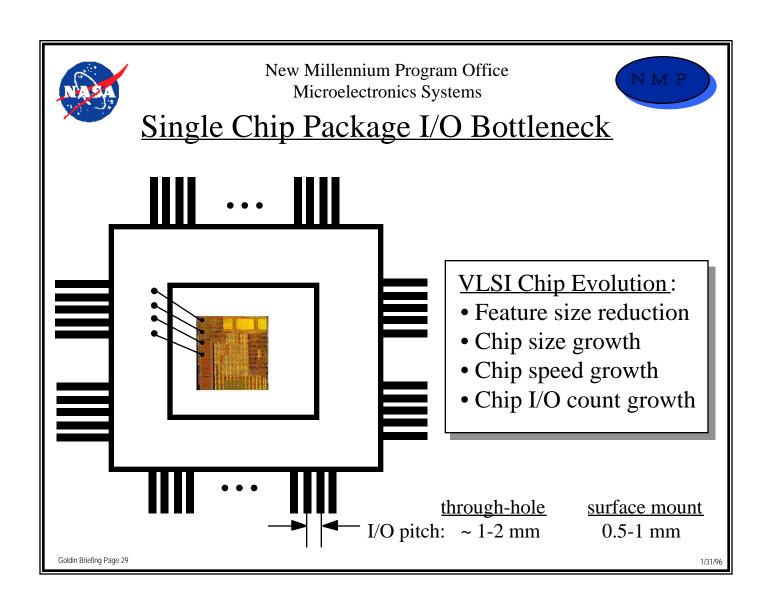


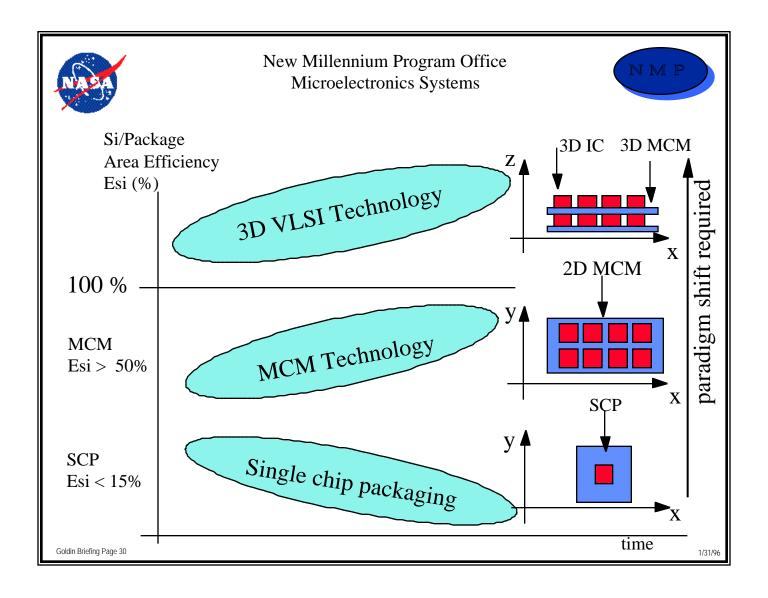


3D VLSI Technology Development

• Eliminating the Single Chip Package Bottleneck

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SRAM Array Interconnect



Local
interconnect
for n*, p*
(tungsten)
diffusion
contacts



Yellow

CGióbal iintecconnect ((TiAA((cu)) TTI/TN))

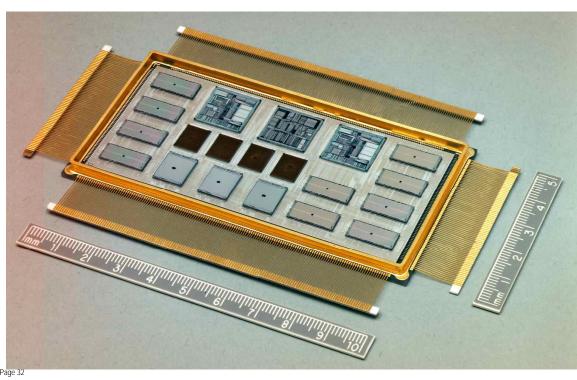
Light Green

Contact
Studs to
global
interconnect
(tungsten)

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NASA's Advanced Flight Computer 33-Chip Multichip Module



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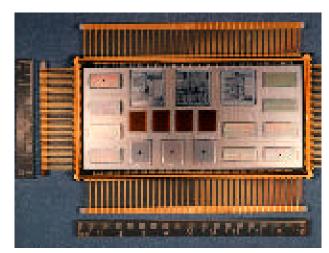
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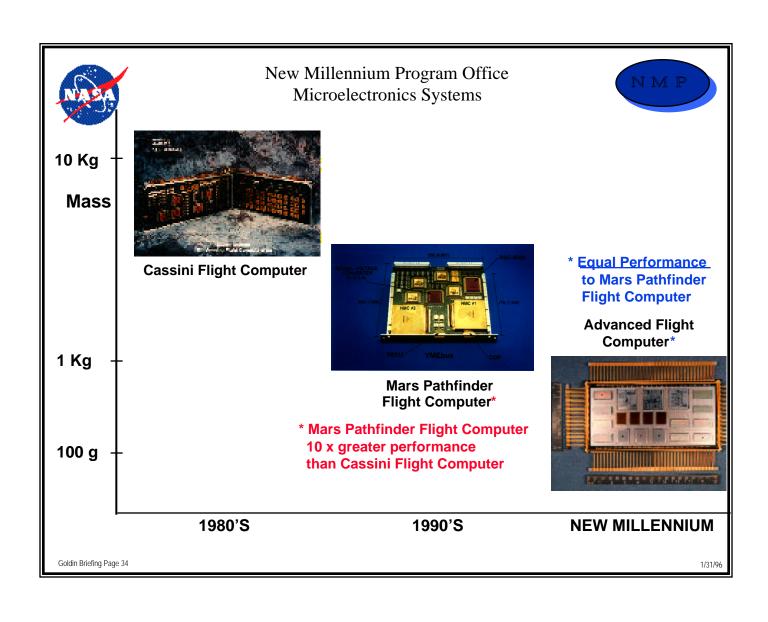
New Millennium Program Office

NASA's 33-Chip Flight Computer Module

- Flight Computer System integrated into a single MCM of 33 chips.
- 3D IC stacking used for SRAM and EEPROM memory.
- Si Substrate for inter-chip connections.
- MCM-D Al metal and SiO2 dielectric.
- Mass < 100 grams (89 grams)
- Volume < 1.5 ci
- AlN 442 leaded package
- Rad-hard, R3000 ISA, TRW RH-32
- 20 MIPS @ 25 MHz and < 12 watts
- Industry partnership: TRW, nCHIP.
- Flight validation on SSSTI 7/96.

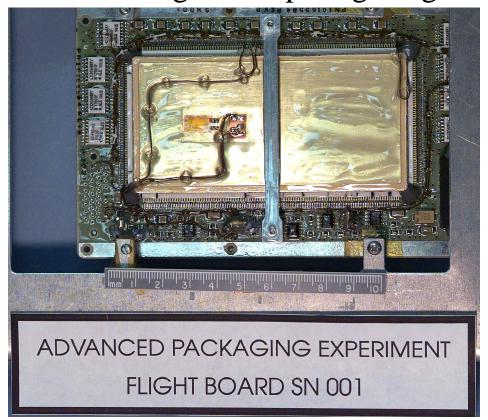


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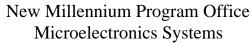




Advanced Flight Computing Program



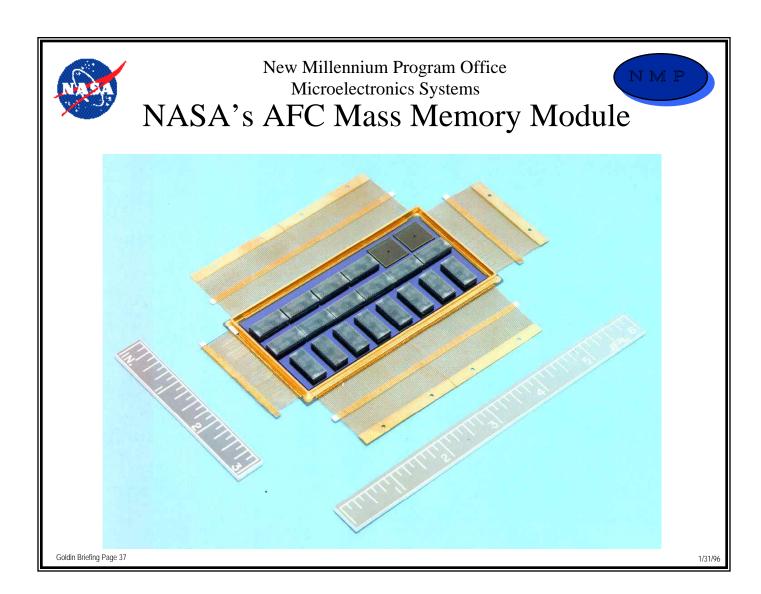
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Advanced Flight Computing Program

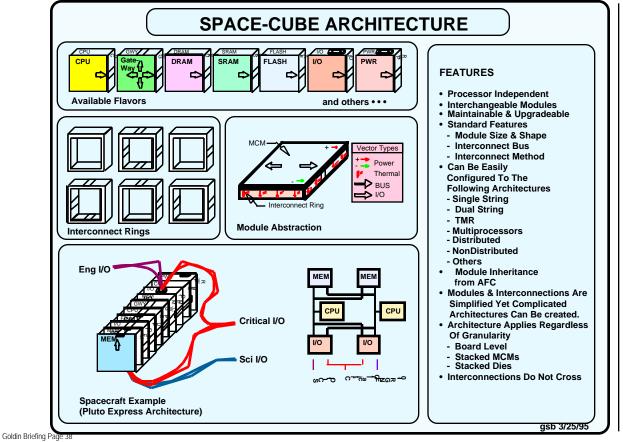


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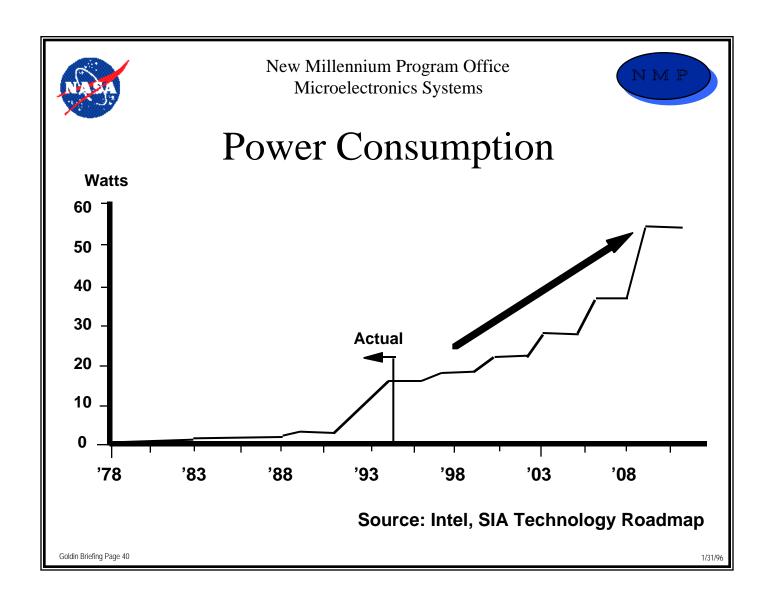
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Low-Power Electronics Technology Development

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Key Drivers for Voltage Scaling

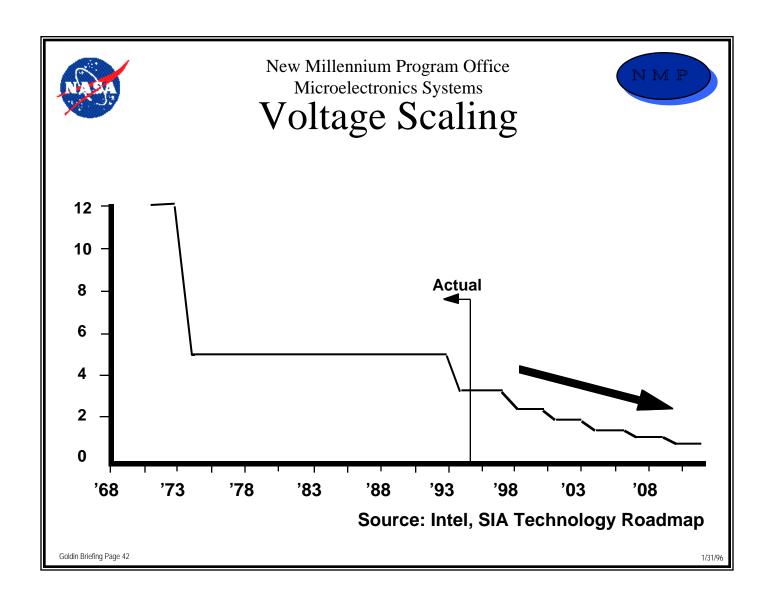
• Reduced Power dissipation, P:

$$P = f \bullet c \bullet v^2 \bullet$$

- Higher Reliability
- Reduced Transistor Channel length
- Extended Battery Lifetime

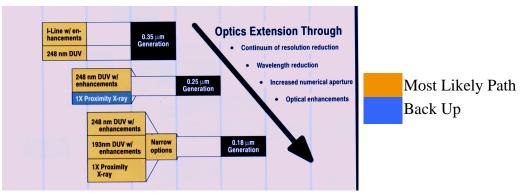
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1989 1992 1995 1998 2001 2004 2007 2010



- MIT Lincoln Laboratory has production worthy i-line and 248 nm DUV wafer steppers, as well as the world's only 193 nm DUV wafer step and scan system. All three tools are operating in Lincoln's class-10 semiconductor fabrication facility, allowing future deepsubmicrometer technologies to be investigated today.
- This advanced optical lithography capability is currently being used to develop a sub 0.25 μm low power (V_{DD} = 0.9 V) SOI CMOS process technology suitable for a wide range of low power, high performance applications.

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193-nm PROJECTION LITHOGRAPHY

193-nm LITHOGRAPHY SYSTEM



LINCOLN LABORATORY 193-nm EXPOSURE SYSTEM

• SPECIFICATIONS

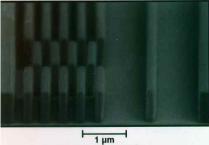
- ArF EXCIMER LASER SOURCE
- 0.5 NA OPTICS
- 4x REDUCTION PRINTING
- 22 x 32.5 mm EXPOSURE FIELD
- BASED ON SVGL MICRASCAN II STEP AND SCAN

RESOLUTION

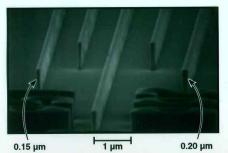
- 0.18 TO 0.25 µm WITH CONVENTIONAL PHOTOMASK
- 0.10 µm WITH PHASE-SHIFT PHOTOMASK

• STATUS

- INSTALLED IN MICROELECTRONICS LABORATORY
- HIGH RESOLUTION ACHIEVED OVER FULL FIELD
- OFF-AXIS ALIGNMENT INSTALLED
- AUTOMATIC WAFER HANDLING SYSTEM INSTALLED
- BEING QUALIFIED JOINTLY WITH INDUSTRY



0.20 µm FEATURES



ISOLATED LINES

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SILICON-ON-INSULATOR TECHNOLOGY FOR LOW POWER ELECTRONICS

PROGRAM HIGHLIGHTS:

UTILIZES WORLD'S MOST ADVANCED OPTICAL LITHOGRAPHY TECHNOLOGY.
- INITIAL WORK USING 245-nm LITHOGRAPHY WITH TRANSFER TO 193-nm LITHOGRAPHY

LOW POWER OPERATION, 1 VOLT SUPPLY, 0.3 VOLT THRESHOLDS.

FULLY-DEPLETED DEVICE DESIGN FOR REDUCED PARASITIC CAPACITANCES AND NEAR IDEAL SUBTHRESHOLD SLOPES.

PROCESS HIGHLIGHTS:

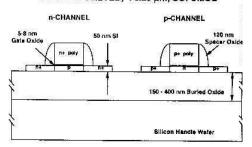
50 nm ACTIVE SILICON THICKNESS WITH COMPLETE OXIDE ISOLATION.

DUAL-DOPED POLY FOR COMPLIMENTARY THRESHOLD MATCHING.

SELF-ALIGNED SHALLOW SILICIDE PROCESS WITH OXIDE SPACERS.

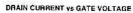
ALUMINUM REFLOW CONTACT FILL TECHNOLOGY.

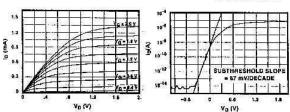
FULLY-DEPLETED, < 0.25 μm , SOI CMOS



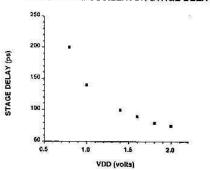
n-CHANNEL TRANSISTOR CHARACTERISTICS (W/L = 6 μm/0.25 μm)

DRAIN CURRENT VS DRAIN VOLTAGE





0.25 um RING OSCILLATOR STAGE DELAY



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Low Power Electronics Development Approach:

- Collaborate with ARPA on the ULPE Program
- Work with Industry: Intel, IBM, Motorola
- Work with Academia: USC, GIT, Stanford
- Work with other National Labs: MIT/LL, SNL
- Fly LPE Experiment on DS1:
 0.18μ SOI, 1 volt technology
- Initiate LPE R&D task at JPL in FY 96

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New Millennium Program Office Microelectronics Systems Low Power Electronics

R&D at JPL



- LPE Library Development
- Circuit Design, Simulation, and Test
- Radiation Test and Analysis
- Physics of Failure Analysis
- Reliability modeling and Analysis
- Low-Power Opto-Electronics Development with Optivision (SBIRs 1 and 2), for Low-Power 1773 s/c bus
- Low-Power Systems Design
- Low-Power Design Synthesis

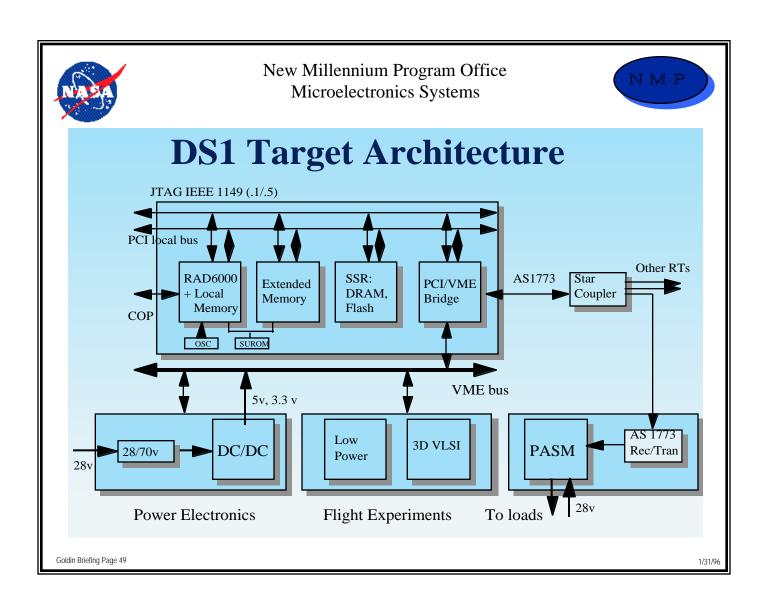
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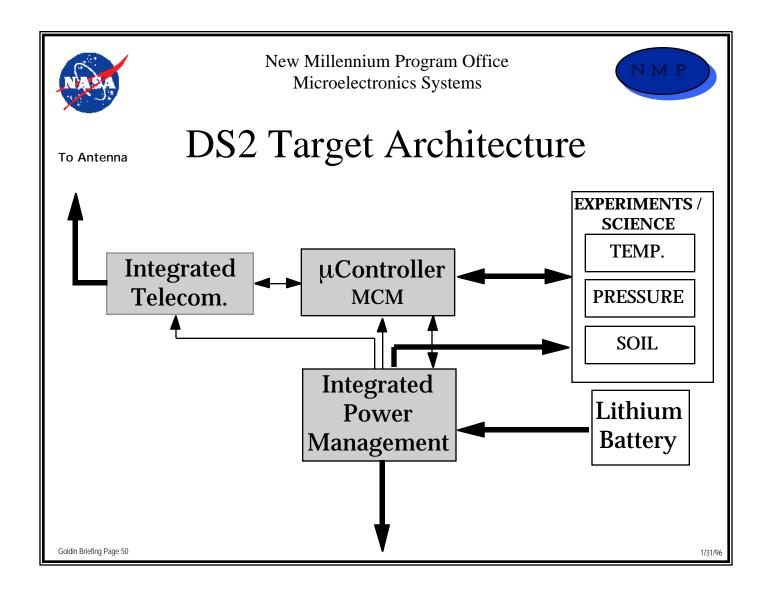


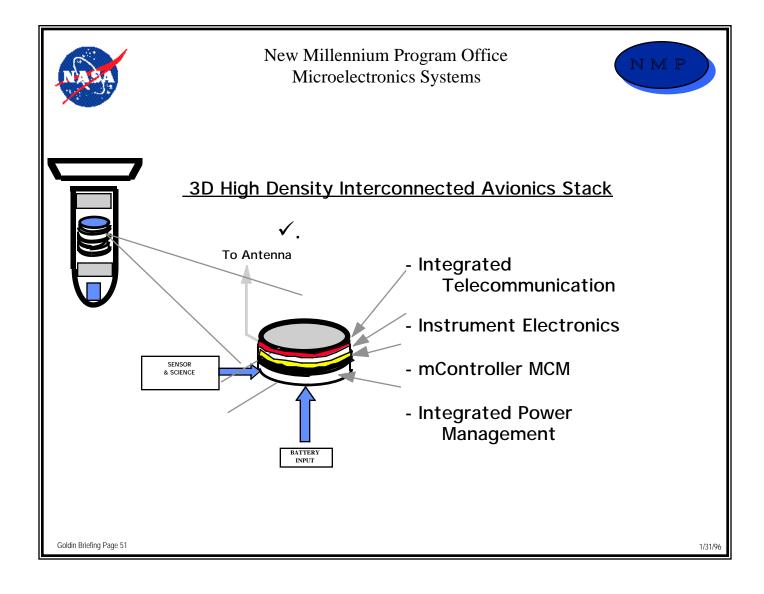


Deep-Space 1 Avionics Architecture

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Customers and Partnerships

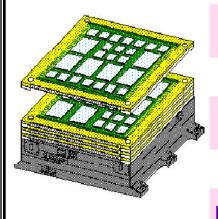
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Pluto Express

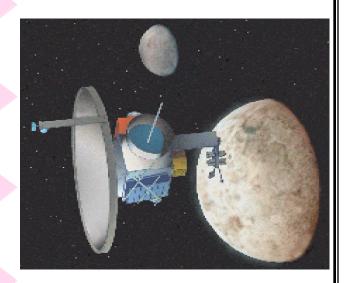
Reliability



Low Power

Fault Tolerance

Miniaturization



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